

Fig. 1

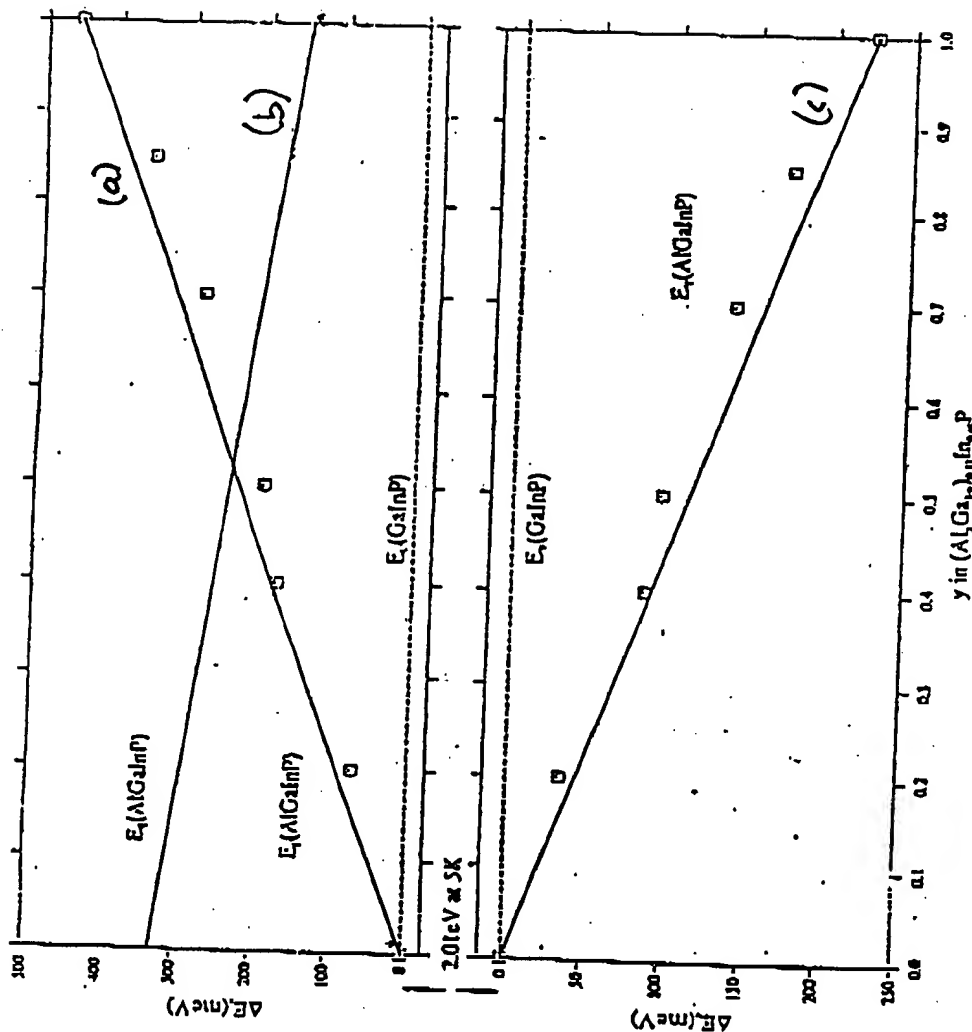


Fig. 1

A diagram of the variation of the $G_{0.52}In_{0.48}P/(AlGa)InP$ heterobarrier height (meV) as a function of aluminium mole fraction in the quaternary alloy assuming a 70:30 band offset ratio.

FIG. 2

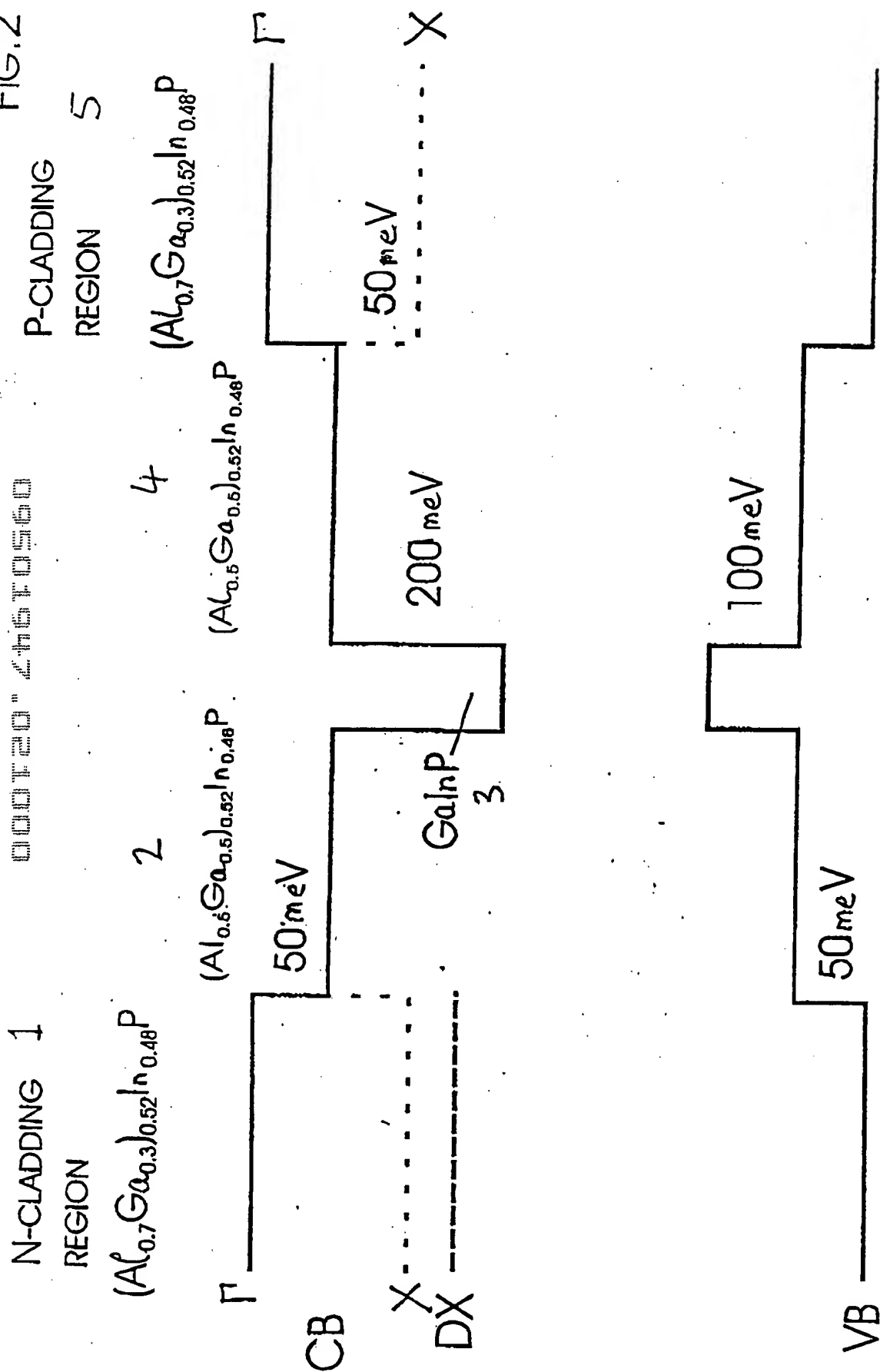
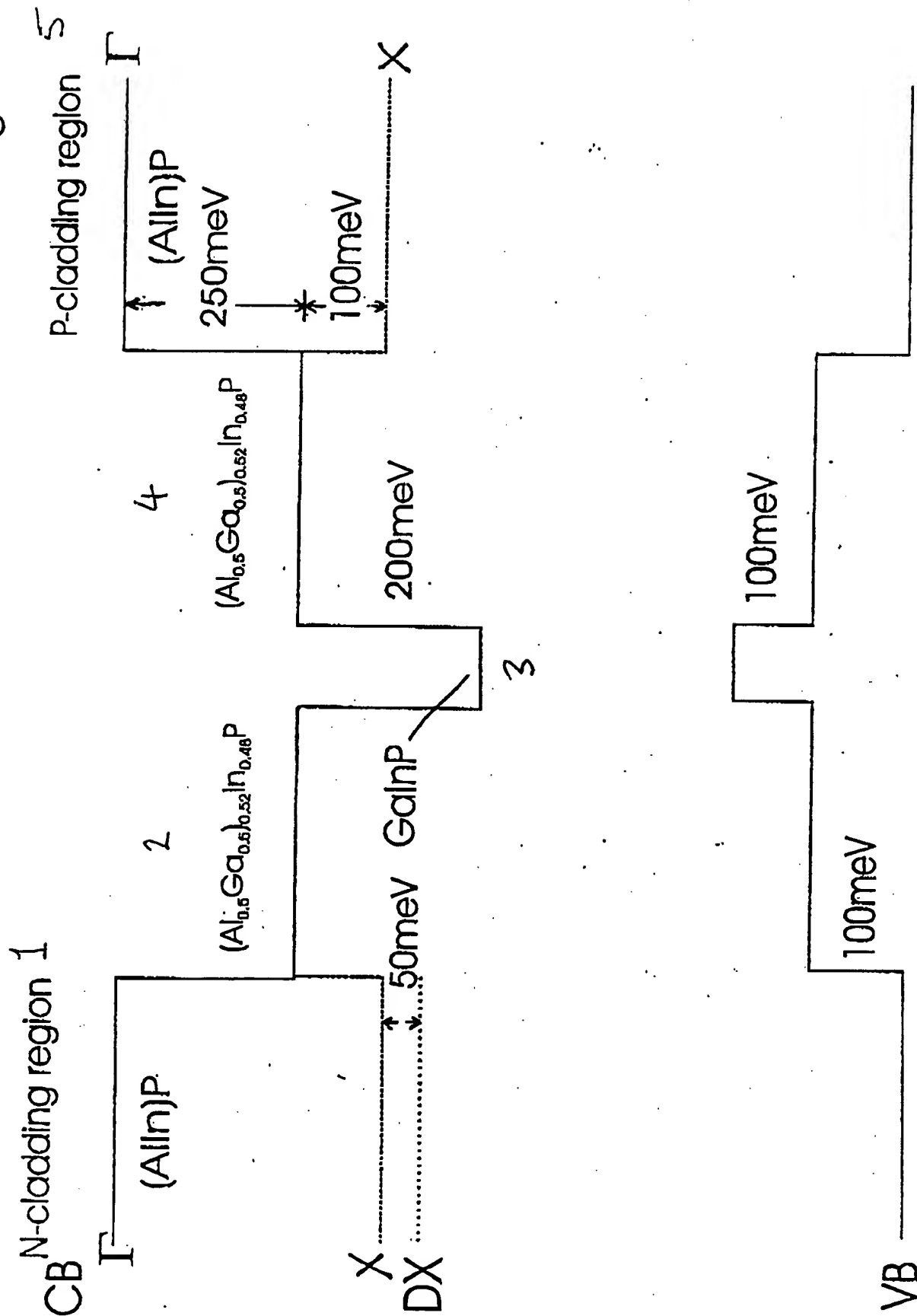


Fig.3

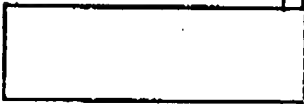


11

N-cladding region

16

AlInP



GaInP

X

CB

Γ

500meV

12

$(Al_{0.4}Ga_{0.6})_{0.5}In_{0.5}P$

13

GaInP



14

$(Al_{0.4}Ga_{0.6})_{0.5}In_{0.5}P$



AlInP

17

P-cladding region

X

GaInP

Γ

VB

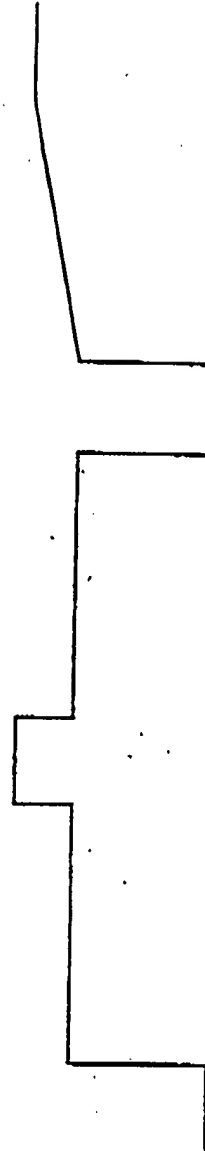


Fig.5

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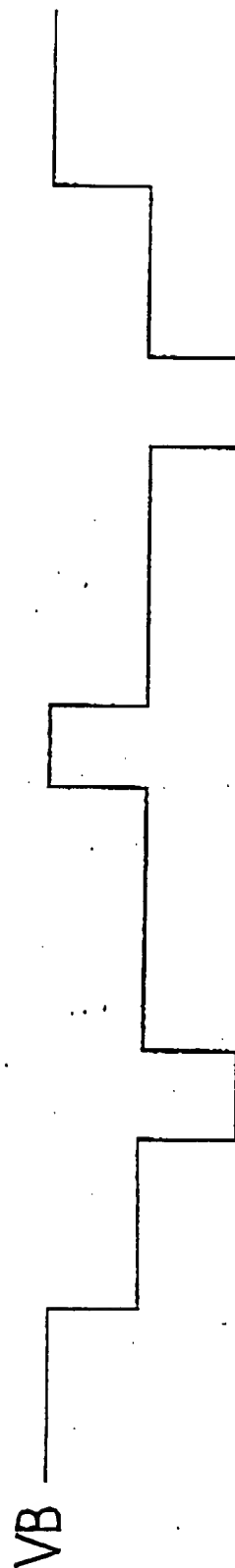
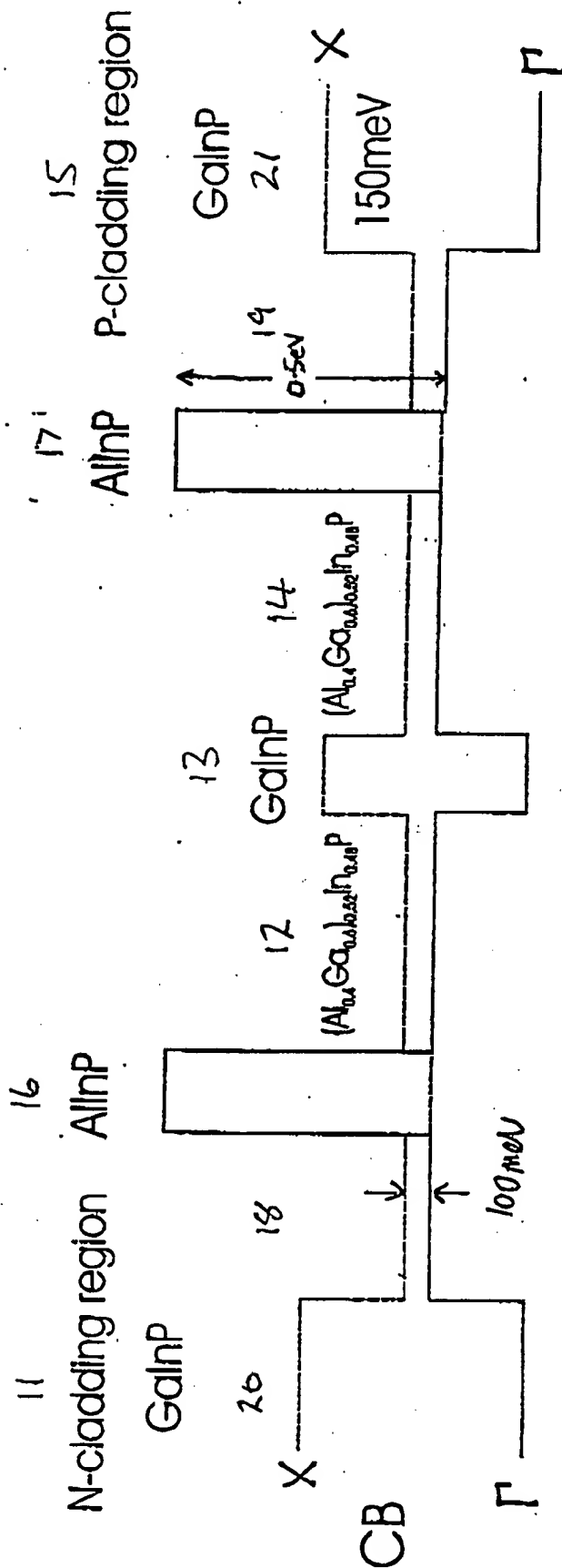
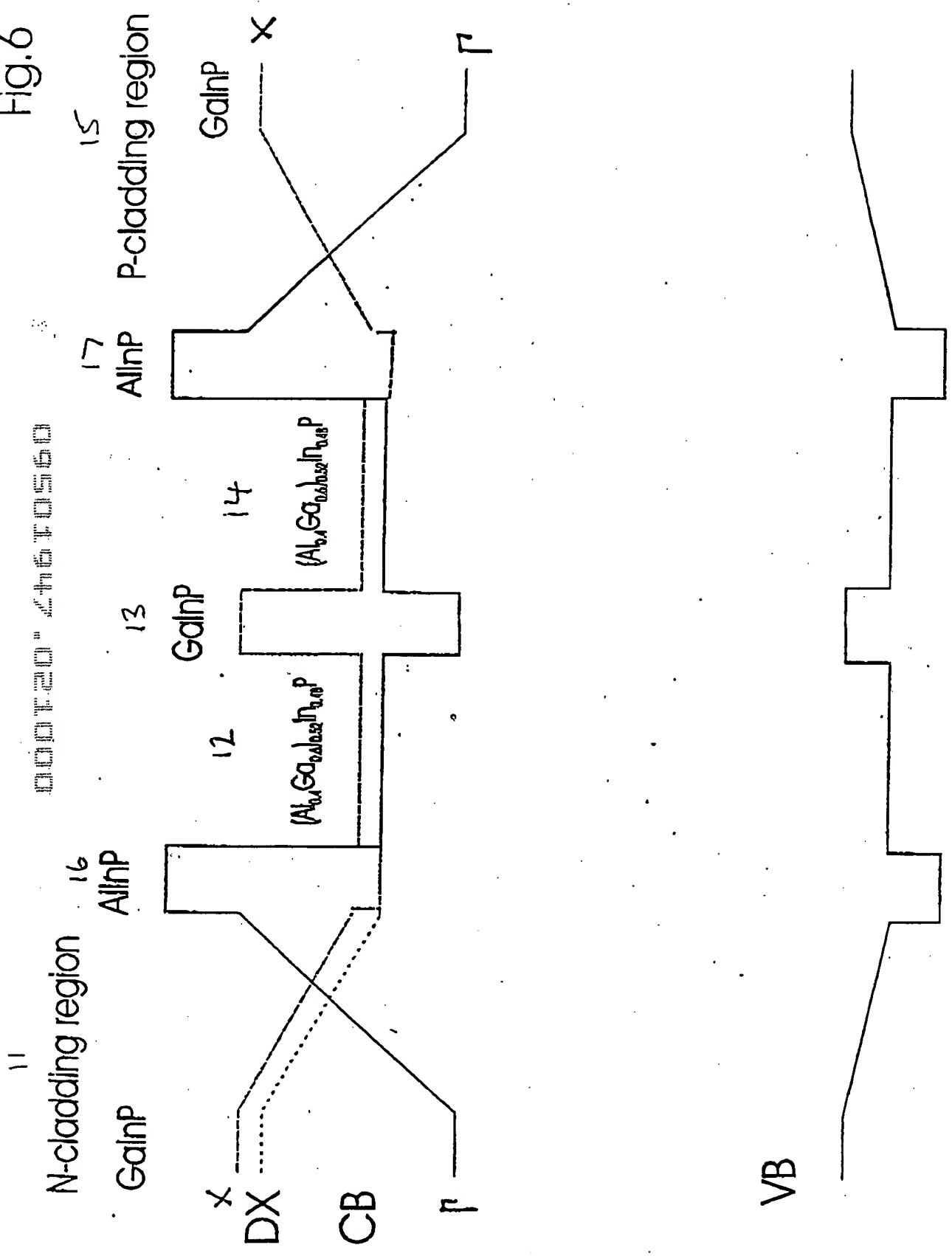
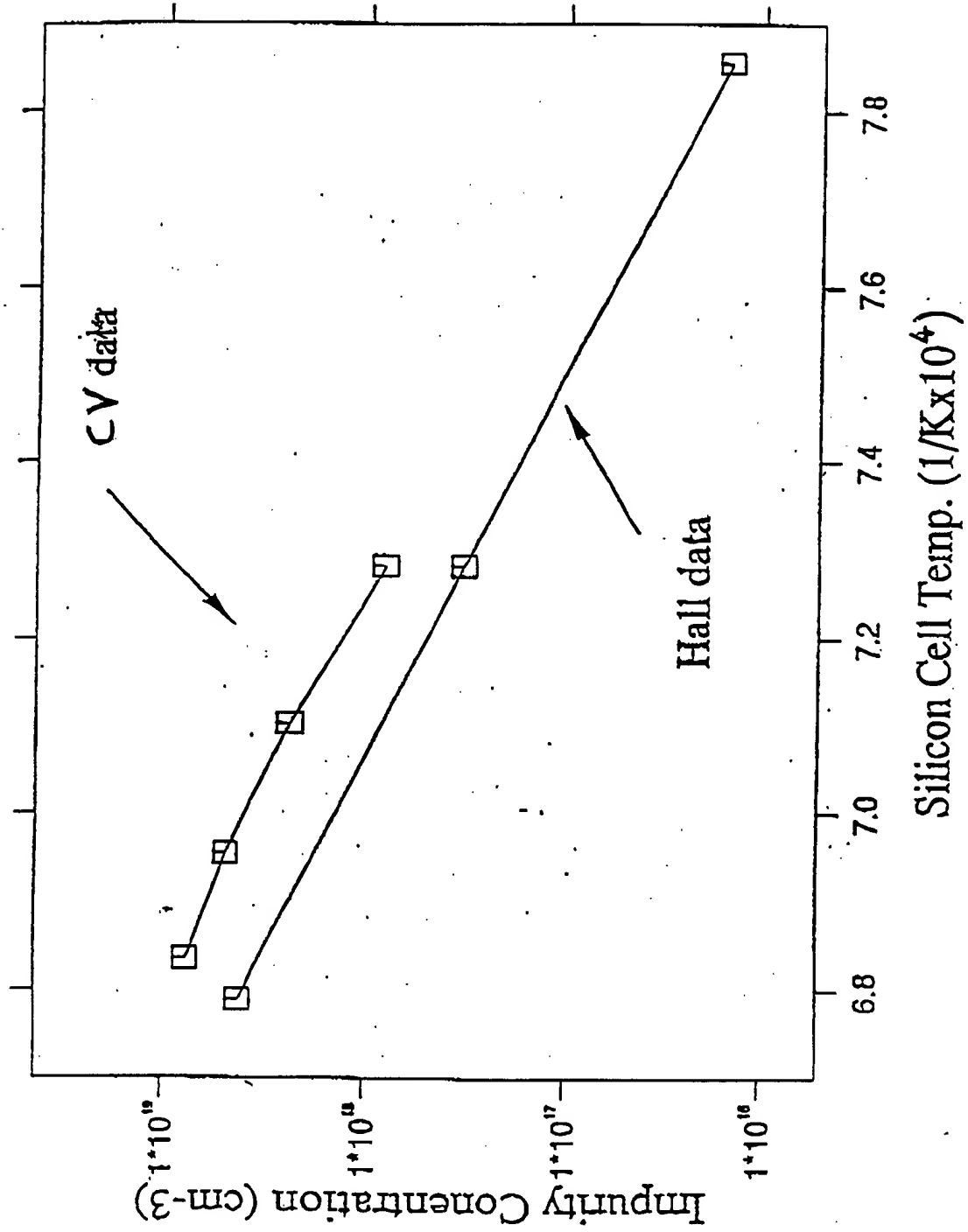


Fig.6

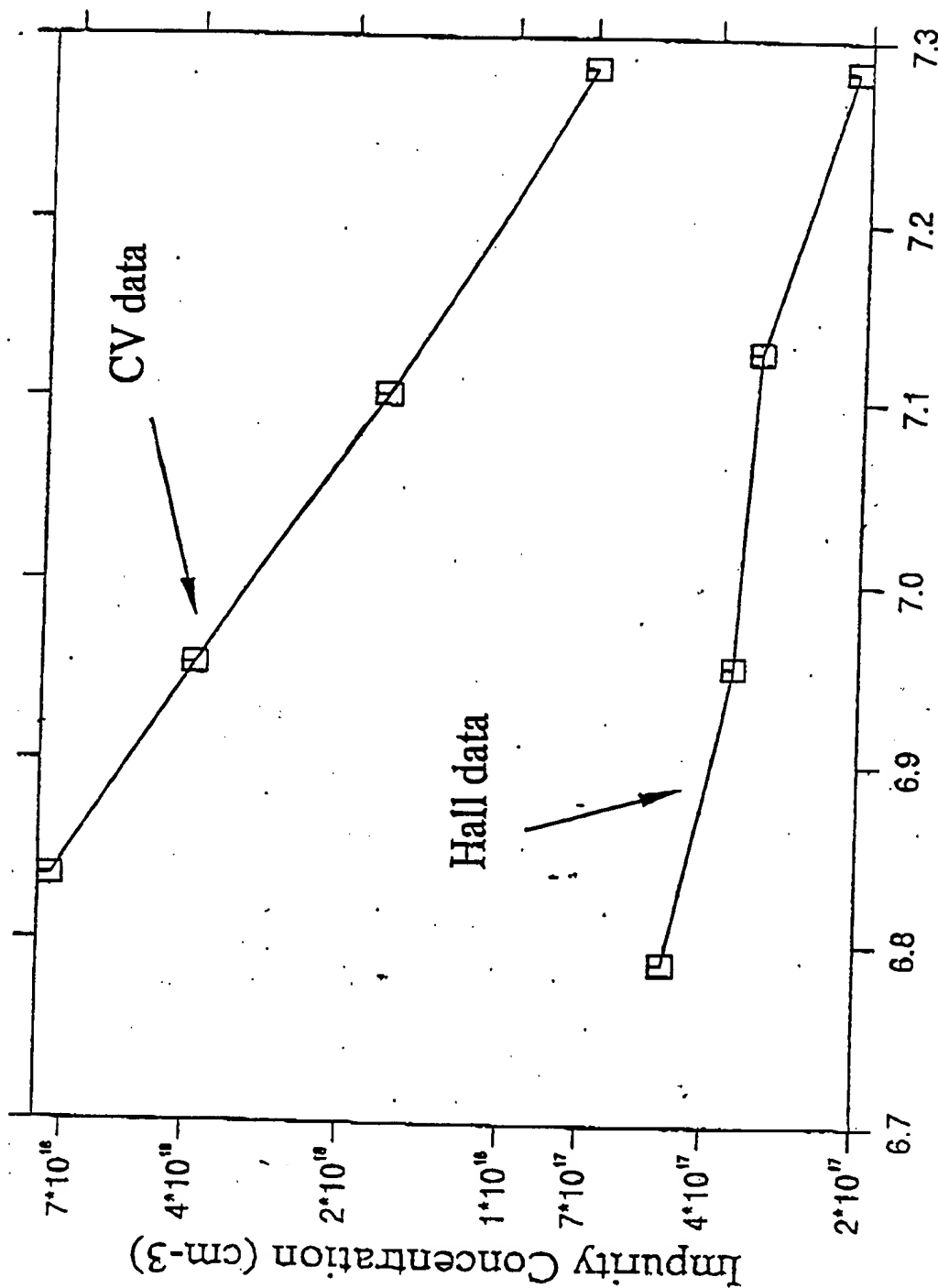


GaInP Silicon Doping



DOTED" 46T050

AlGaInP (y=0.7) Silicon Doping



Silicon Cell Temp. (1/Kx10⁴)

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Fig 9

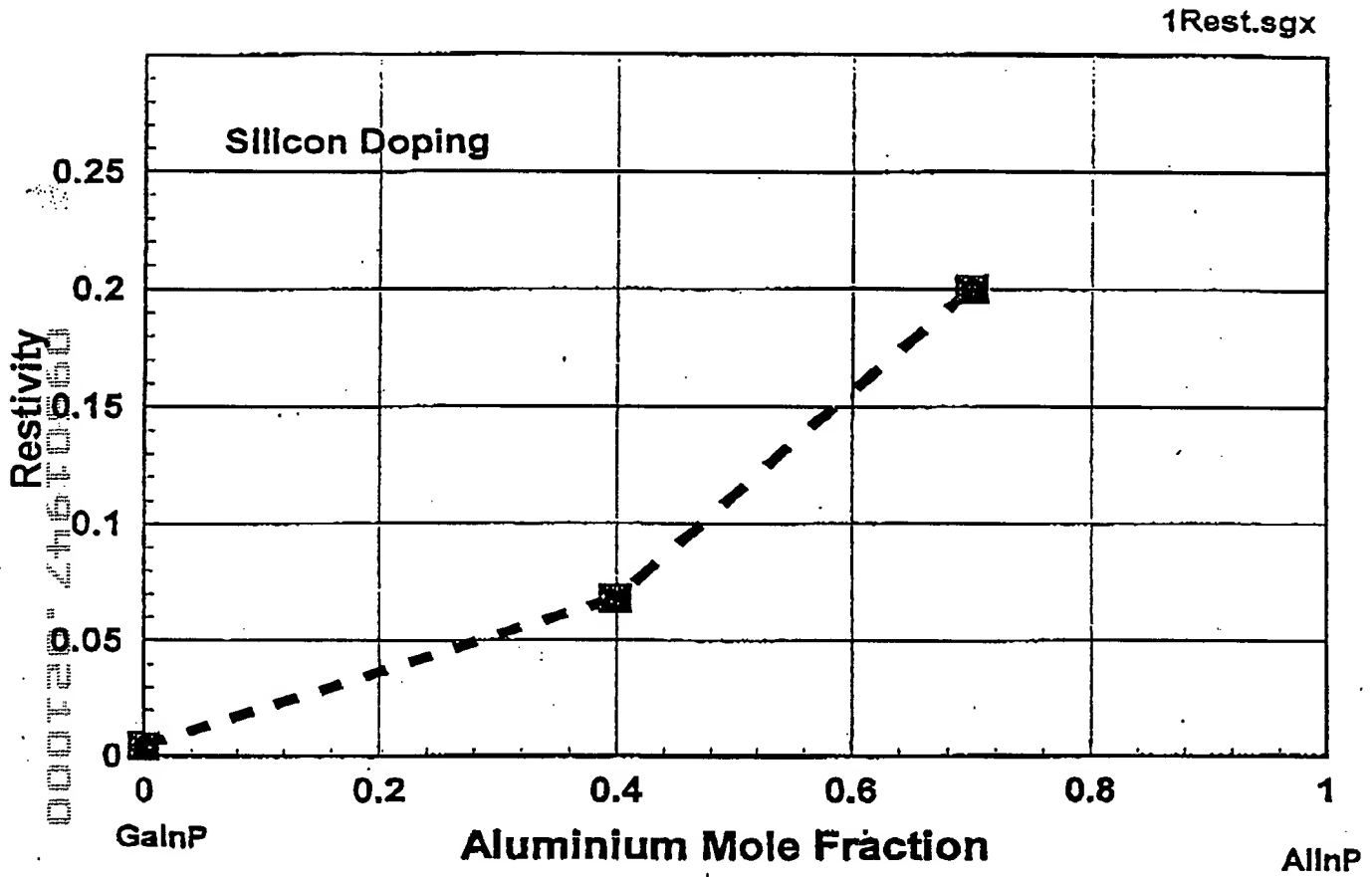


FIG. 9

Figure 10

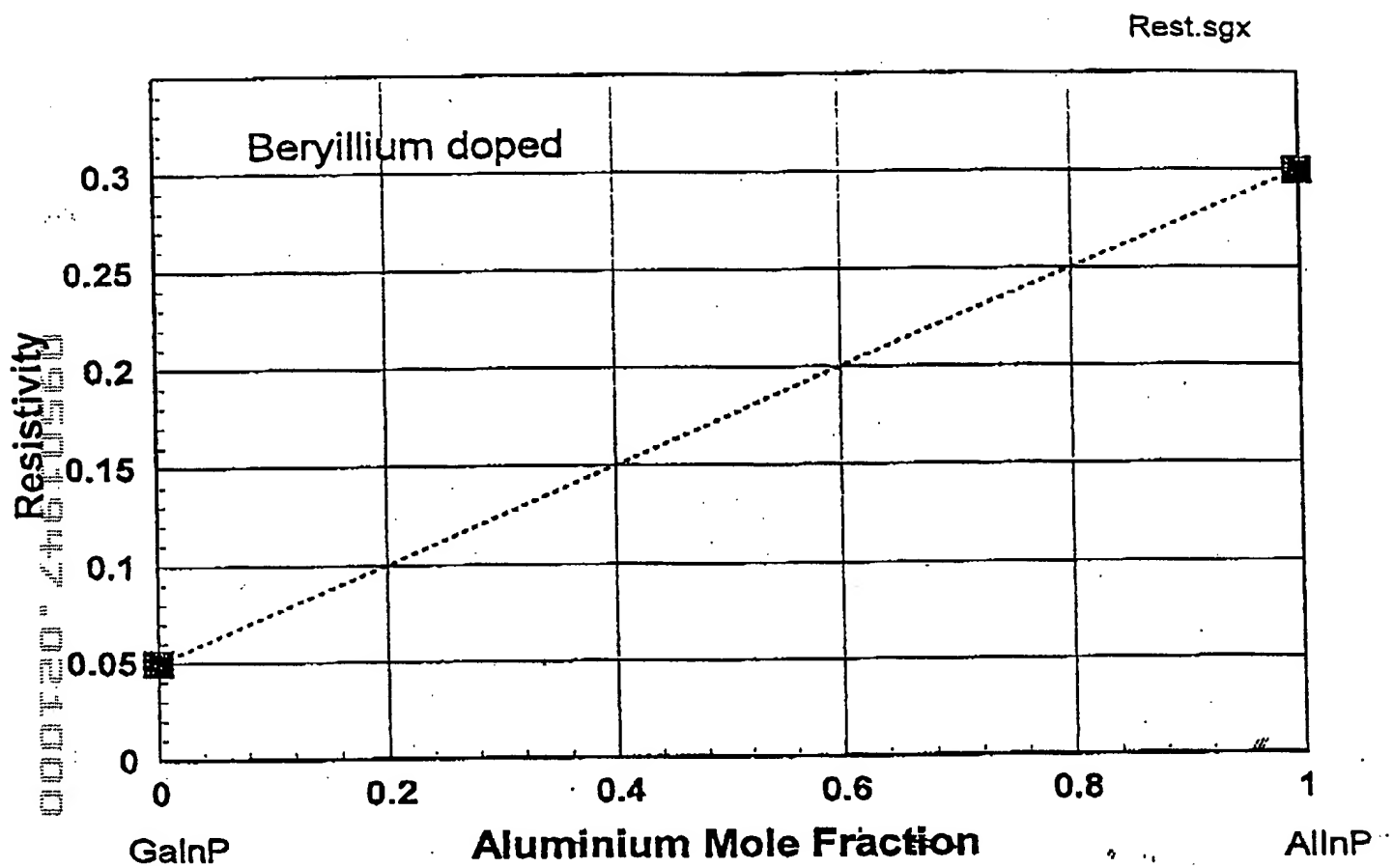
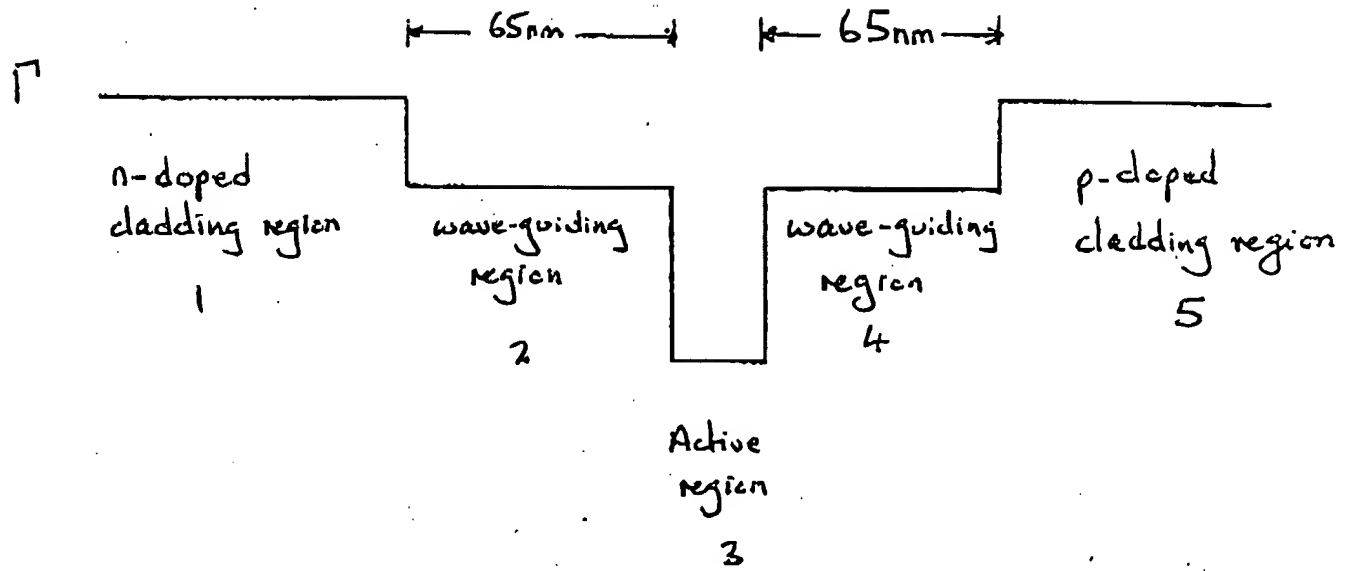
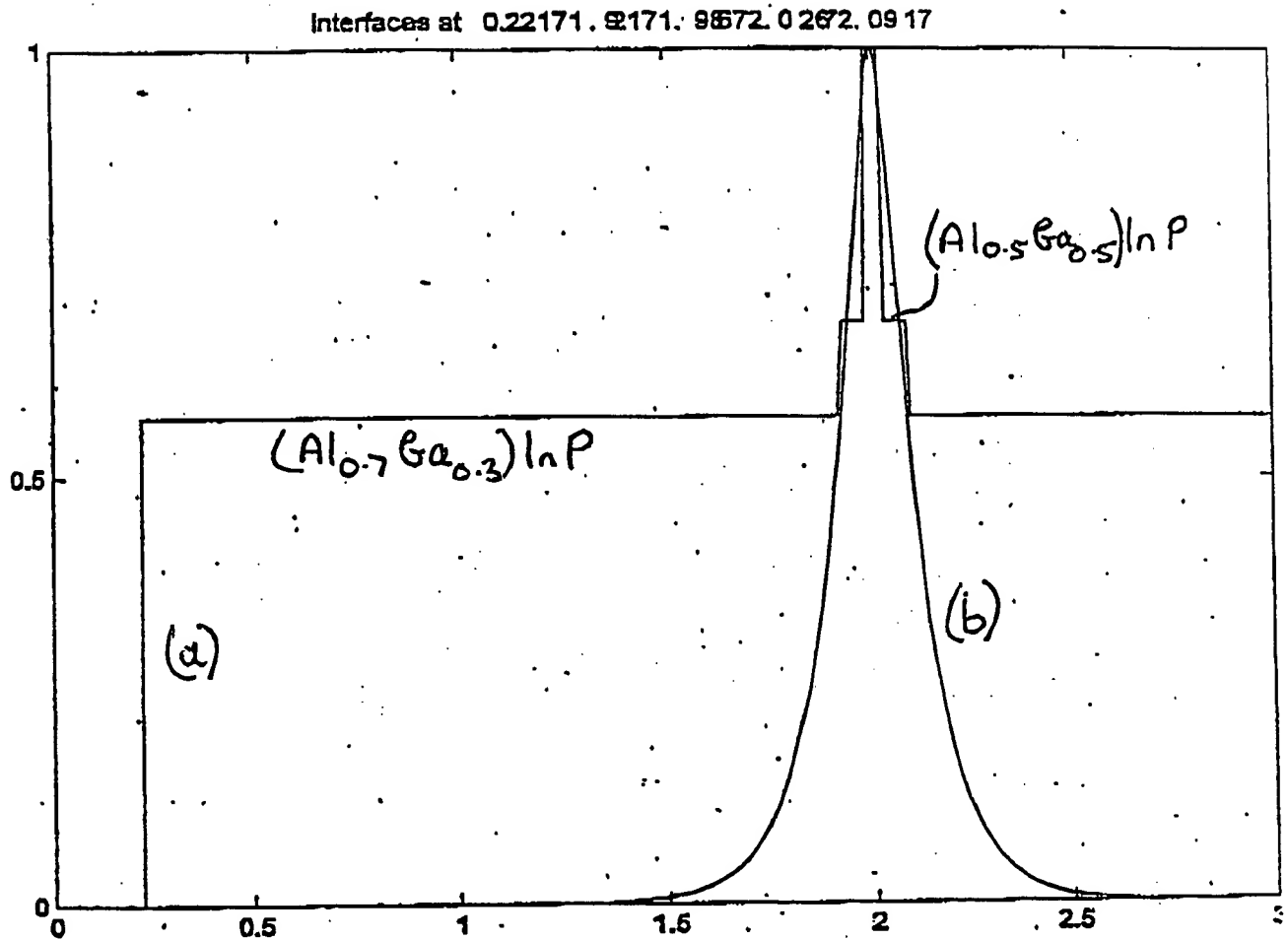


Figure 11 (a)



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Figure 11 (b)



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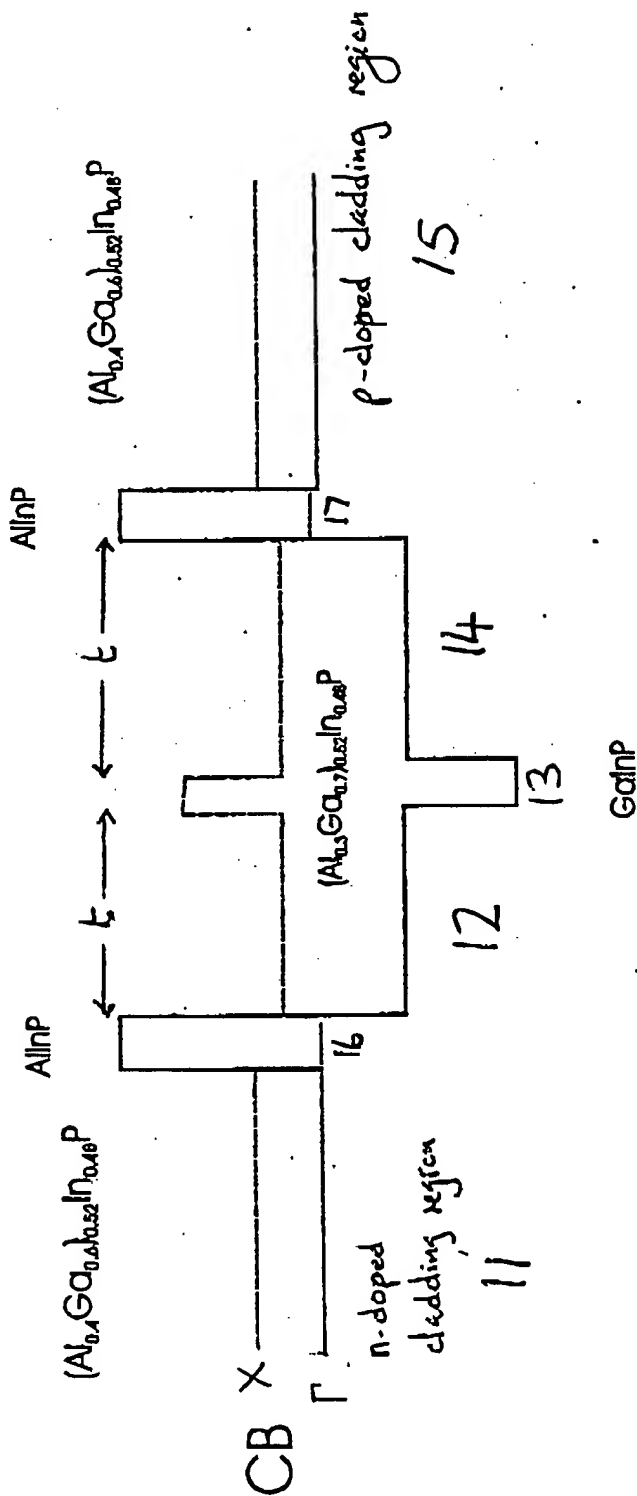
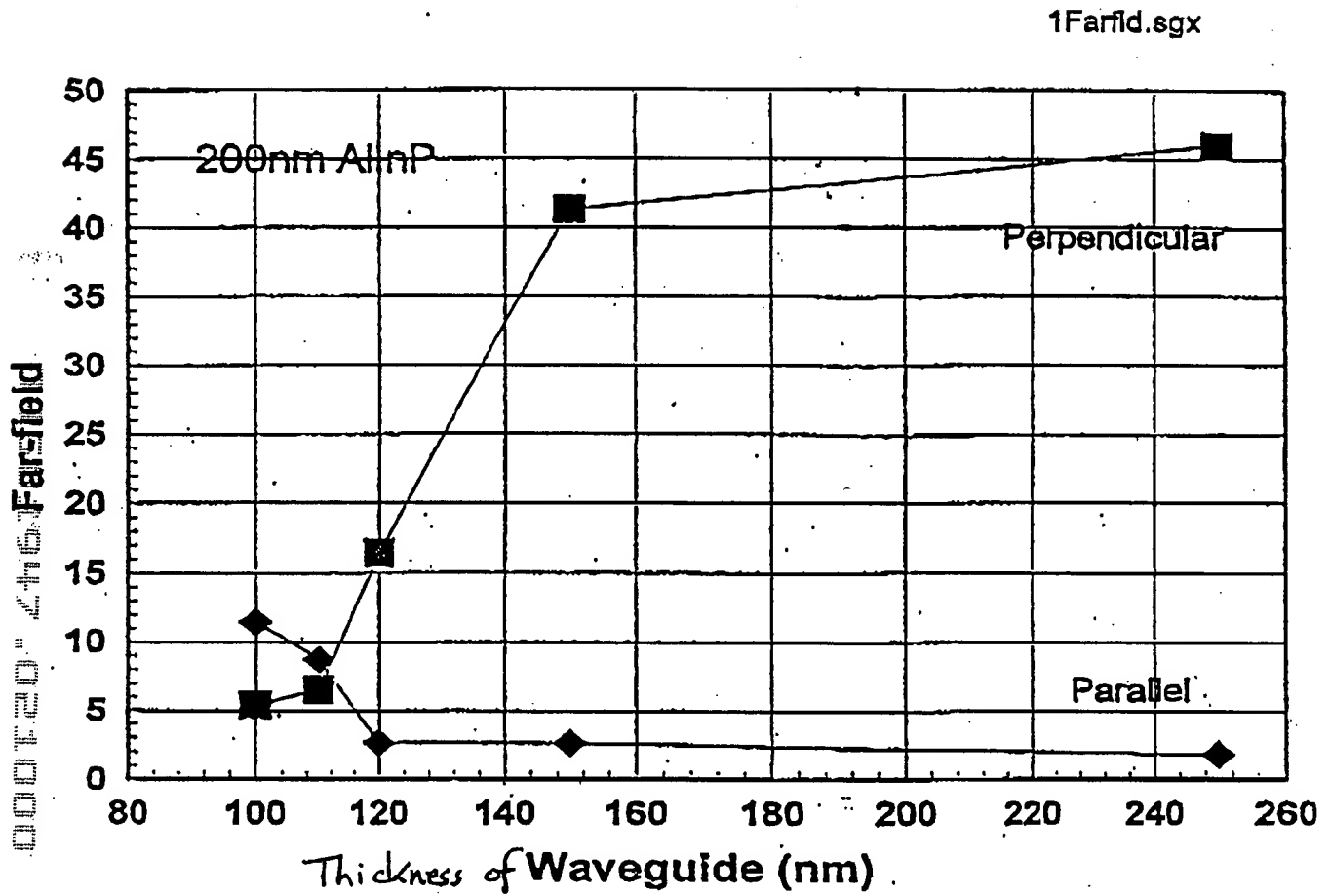


Figure 13(a)



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Figure 13(b)

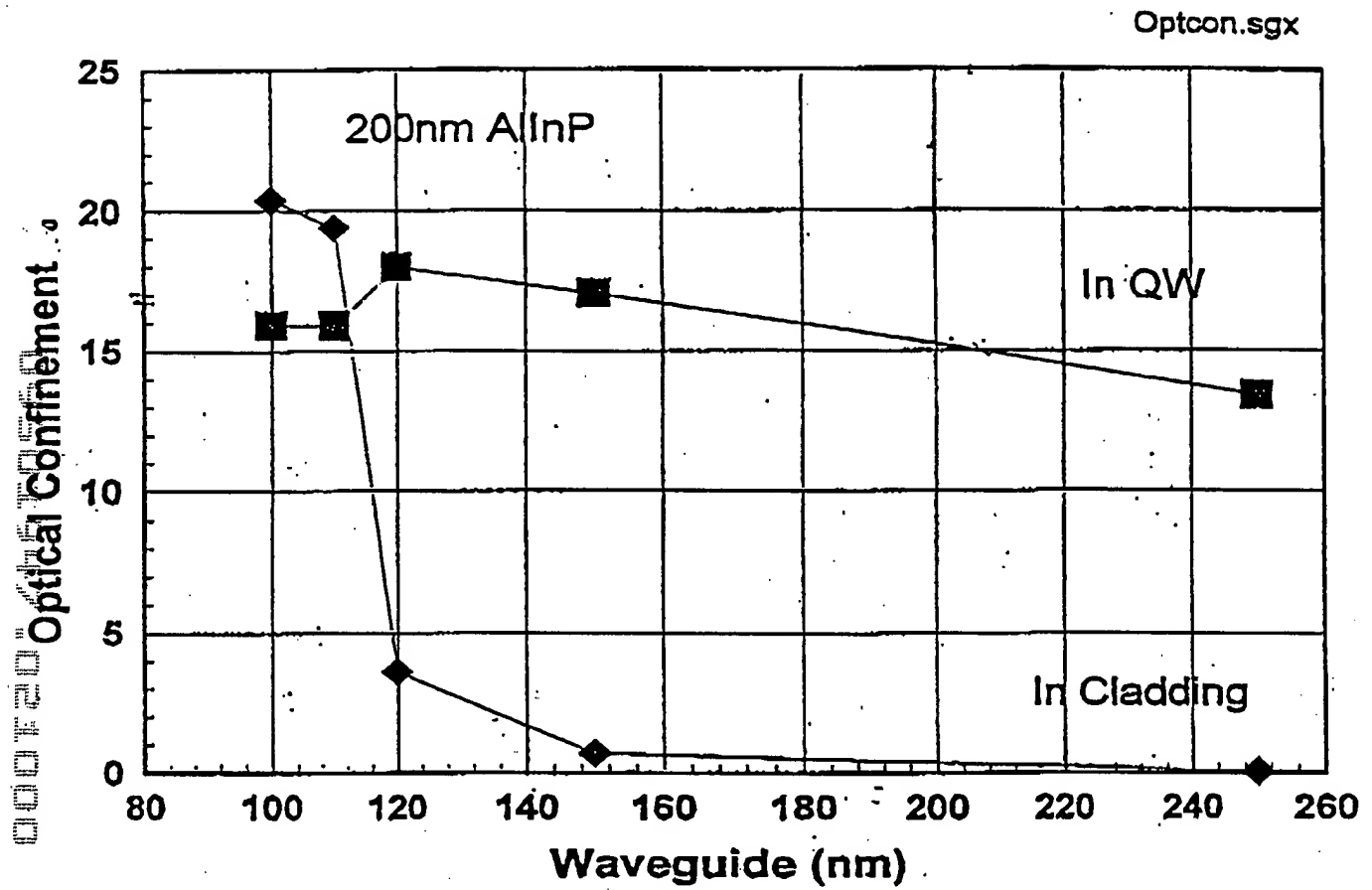
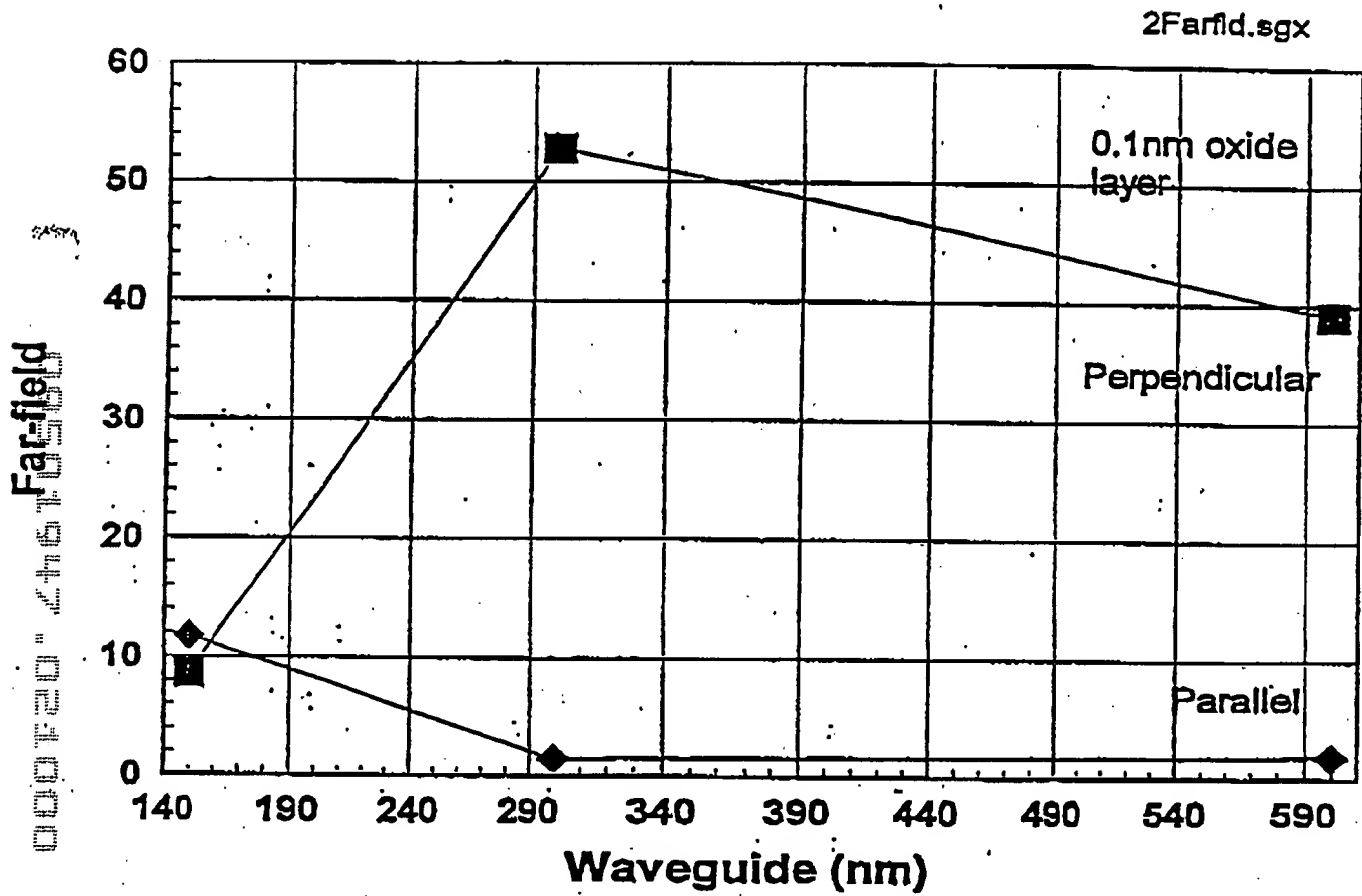


Fig. 13 (b)

Figure 14(a)



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Figure 14(b)

